

Description

The invention relates to a method of testing by means of an energy beam a part of a display device comprising a picture electrode of a pixel to be formed and a switching element between at least one drive line and the picture electrode.

In this Application switching elements are to be understood to mean, inter alia, thin-film transistors (FET's), diodes and, for example, MIM's (metal-insulator-metal) but also, for example, combinations of diodes as are used, inter alia, in diode rings or switching elements comprising a plurality of sub-elements for the purpose of redundancy.

In larger display devices, notably active liquid crystal display devices which are organized as a matrix, the number of switching elements and hence the risk of non-functioning or malfunctioning switching elements increases rapidly. Since the chance of rejection of the finished product increases, there is a need to test intermediate products. A problem is that unlike, for example, semiconductor products, the product cannot be tested functionally at an early stage.

The finished product cannot be tested electrically or electronically because the optical switching must be checked, for example, visually. Since a finished product includes drive electronics, it is a great advantage in view of cost considerations if a sub-product which in itself already comprises a large part of the overall product such as, for example, a first supporting plate of a liquid crystal display device with switching elements, can be tested in a simple manner (and repaired if necessary). Not only does this lead to a reduced number of rejects of the final product but also to material saving (inter alia, liquid crystal material, second supporting plates).

A method of the kind described in the opening paragraph is known from EP-A-0 143 039. In this method the presence of interconnection lines is tested by irradiating photodiodes connecting to said lines. Separate picture electrodes can be tested by introducing a photodiode in each picture element. Such extra provisions render the manufacture of the display device extra complicated, and reduce the effective area of the pixels. Moreover, the light-sensitivity of these photo-diodes may influence the hold characteristics of complete display device in a disadvantageous way.

It is a purpose of the invention to provide a test method in which these problems are overcome.

It is a further object to provide a test method in which no extra provisions in the display device are needed.

To this end a test method according to the invention is characterized in that the switching element is tested by scanning the switching element

or the picture electrode by means of said energy beam in order to detect the functioning or non-functioning of the switching element.

The energy beam may be, for example, an electron beam or a light beam, particularly a laser beam.

In this respect it is to be noted that testing by means of a laser beam or an electron beam for semiconductor arrangements is known per se from IC technology. However, in this technology extra switching elements are generally provided such as thyristors, (German Patent Specification 28,31,787), photosensitive switches (US 3,801,910) or additional supply lines (FR 2,316,728). In the parts to be tested of a display device such extra provisions would render the manufacture of such parts additionally complicated. Similar drawbacks apply to the method of testing display devices as described above in EP-A-0,143,039. Moreover, the finished display device is tested in this case so that all above-mentioned drawbacks apply. In this method a test on the presence of connections is also performed by means of irradiation of additionally provided photodiodes, which is in contradistinction to the method according to the invention in which the actual switching elements are directly tested by scanning them or the associated pixels with an energy beam. Such extra provisions are in principle entirely superfluous when testing by means of the method according to the invention.

The invention will now be described in greater detail by way of example with reference to the accompanying drawings in which

Fig. 1 shows a first example of the method;

Fig. 2 shows a variant of this method for another structural type of the display device;

Fig. 3 shows an example of the method of testing parts of the device as shown in Netherlands Patent Application No. 8,502,663, whilst

Fig. 4 shows examples of the associated test characteristic curves and

Fig. 5 shows a method of testing and, if necessary, repairing a similar part of the device as shown in Fig. 1.

Fig. 1 shows diagrammatically a part of a display device 10 which is in the form of a matrix in this example. The matrix comprises row electrodes 11 and column electrodes 12. At the area of the crossings of row electrodes and column electrodes liquid crystal elements 9 are connected via a switching element, in this example a thinfilm field effect transistor 13, to the row electrodes 11 and the column electrodes 12. The liquid crystal pixels comprise a picture electrode 17 which in this example is arranged on the same supporting plate as the electrodes 11, 12 and the transistors 13. Furthermore the pixels comprise a counter electrode 18 on a second supporting plate which is shown by

means of broken lines in Fig. 1.

According to the invention the part of the device which is present on the first supporting plate is tested first before the two supporting plates are secured together and subsequently the space between the supporting plates is filled with liquid crystal material and then closed. There are different possibilities for this purpose.

According to a first method the gate 15 of the thin film field effect transistor 13 can acquire such a voltage via the row electrode 11 that the transistor 13 is turned on. Simultaneously with the selection of a transistor 13, for example, the picture electrode 17 connected to the drain zone 16 of the transistor is given a quantity of negative charge. This may be done by scanning the relevant picture electrode 17 with an electron beam 7. The charge present on the picture electrode can subsequently be detected via the conducting transistor 13 and the column electrode 12 (which is connected to the source zone 14 of the transistor 13) with the aid of means which are generally known. The detection or non-detection of the charge is an indication of a transistor 13 functioning properly or improperly or of interconnections which are present or not present.

Conversely, the picture electrodes 17 can be given a charge via the transistors 13 by selecting a transistor 13 via a row electrode 11 and by giving the source zone 14 such a voltage via a column electrode 12 that the associated picture electrode 17 is charged. The charge of the picture electrode 17 can then be detected again by scanning with an electron beam 7 in a scanning electron microscope. This provides the possibility of fault detection.

The row electrodes 11 may be selected directly via connection terminals 6 but, if desired, also via an auxiliary circuit 8 in which a plurality of radiation-sensitive switching elements, in this example photo-sensitive diodes 19, are provided between the connection terminals 6 of the row electrodes 11 and a test voltage line 20. By irradiating one of the diodes 19 with radiation 21 of suitable wavelength this diode becomes conducting and the associated row electrode 11 acquires the desired voltage.

Fig. 2 shows a part of a similar matrix in which the switching elements are now constituted by diodes 22, whilst the column electrodes 12 and the row electrodes 11 are now arranged on different supporting plates. The part comprising the row electrodes 11, the diodes 22 and the picture electrodes 17 can be tested similarly as described with reference to Fig. 1. The column electrodes 12 (shown by means of solid lines) and the counter electrode 18 are arranged on the second supporting plate.

Fig. 3 shows diagrammatically a part of another display device 10 with a drive circuit which is suitable for the drive mode as described in Netherlands Patent Application no. 8,502,663. Since all diodes 23 are parallel arranged between the row electrodes 11a, 11b, separate electrical testing is not possible. The pairs (or each of the diodes 23 separately) may be irradiated by means of a laser beam 5. The diodes 23 are considered to be manufactured of a photosensitive material such as, for example, amorphous silicon. Under the influence of the irradiation a photocurrent I_{γ} starts flowing between the row electrodes 11a, 11b whose characteristic can be tested in a manner which is generally known. (In this case the voltage at row electrode 11a is assumed to be higher than that at row electrode 11b).

The column electrodes 12 and the counter electrodes 18 are present on the other supporting plate and can therefore not be used in the test.

If one of the two diodes is not connected or if a connection is interrupted in another way, the photocurrent does not lead to a change in the current measured. The current voltage characteristic (curve a in Fig. 4) may also show deviations due to a too high series resistance (curve b in Fig. 4), or, for example, a too low parallel resistance (curve c in Fig. 4) or a short circuit. With the aid of the current measured at, for example, a test voltage V_m (Fig. 4) it is then possible, for example, to test the presence of the diodes 23 but also to realise a certain form of process control and quality control. The diodes 24 can be tested in a similar manner.

In all examples shown it holds that the switching elements may have a multiple form for the purpose of redundancy. In Fig. 5 the field effect transistor 13 of the device of Fig. 1 is in a dual form of transistors 13a, 13b. In principle the row electrode 11 is connected to the gate of transistor 13a and extends almost as far as the gate of transistor 13b. If it appears that during a test as described with reference to Fig. 1 transistor 13a is not connected or is malfunctioning in another way, it is possible to provide a joint 26 between the row electrode 11 and the gate of transistor 13a by means of the laser beam 25. If necessary, the same laser beam 25 may also be used to remove the connection between the row electrode 11 and the gate of transistor 13a or the connection between transistor 13a and other elements (such as the connection 27 with picture electrode 17). On the other hand the two transistors 13a, 13b may already be both connected in advance whilst after charging of picture electrodes 17 with an electron beam after transistor 13a, 13b can be irradiated by means of a laser beam so that a fault detection can be carried out. If necessary, the connection of a malfunctioning transistor can then be interrupted

again by means of a laser beam.

The invention is of course not limited to the examples shown but several variations which are well known to those skilled in the art are possible within the scope of the invention. Switching elements such as diode rings can be alternatively tested by means of laser radiation; a condition is that the diodes associated with the diode ring are laterally separated. The method described with reference to Fig. 2 may be alternatively used for switching elements other than diodes such as, for example, varistors, MIMs or other dipoles. Likewise the field effect transistors in the example of Fig. 1 may be replaced by other threepoles. In a possibility auxiliary circuit 8 the number of photodiodes 19 may be alternatively reduced by connecting one photodiodes 11, whilst radiation-sensitive resistors instead of photodiodes can be used alternatively. Finally the parts of the devices to be tested need not necessarily form part of a display device which is organised as a matrix, whilst the invention can be alternatively used for display devices other than liquid crystalline devices.

Claims

1. A method of testing by means of an energy beam (5, 7) a part of a display device (10) comprising a picture electrode (17) of a pixel to be formed and a switching element (13, 22, 23, 24) between at least one drive line (11, 12) and the picture electrode (17) characterized in that the switching element (13, 22, 23, 24) is tested by scanning the switching element (13, 22, 23, 24) or the picture electrode (17) by means of said energy beam (5, 7) in order to detect the functioning or non-functioning of the switching element (13, 22, 23, 24).
2. A method as claimed in Claim 1, characterized in that the energy beam is an electron beam (7).
3. A method as claimed in Claim 2, characterized in that the picture electrode (17) is charged by the electron beam (7) and in that the functioning or non-functioning of the switching element (13, 22, 23, 24) is tested by discharging the picture electrode (17) via the switching element (13, 22, 23, 24).
4. A method as claimed in Claim 2, characterized in that the picture electrode (17) is provided with a charge via the switching element (13, 22, 23, 24) and in that the supply of charge to the picture electrode (17) is tested by means of a scanning electron microscope.
5. A method as claimed in Claim 1, characterized in that the energy beam is a light beam (5), particularly a laser beam.
6. A method as claimed in Claim 5, characterized in that the switching element (13, 22, 23, 24) includes at least one photosensitive semiconductor element which is scanned by the light beam (5).
7. A method as claimed in Claims 1 to 6, characterized in that the switching element (13, 22, 23, 24) comprises redundant elements which, dependent on the test result, can be incorporated in or removed from the interconnection between the drive line (11, 12) and the picture electrode (17).
8. A method as claimed in Claim 7, characterized in that a laser beam is used for establishing or interrupting the interconnection.
9. A method as claimed in Claims 5 to 8, characterized in that the photosensitive semiconductor elements are laterally separated.

Patentansprüche

1. Verfahren zum Prüfen mittels eines Energiebündels (5, 7) eines Teils einer Anzeigeanordnung (10), mit einer Bildelektrode (17) eines zu formenden Bildelements und mit einem Schaltelement (13, 22, 23, 24) zwischen wenigstens einer Steuerleitung (11, 12) und der Bildelektrode (17), dadurch gekennzeichnet, daß das Schaltelement (13, 22, 23, 24) durch Abtasten des Schaltelements (13, 22, 23, 24) oder der Bildelektrode (17) mittels des Energiebündels (5, 7) geprüft wird, um die gute oder nicht gute Wirkung des Schaltelements (13, 22, 23, 24) zu detektieren.
2. Verfahren nach Anspruch 1, dadurch gekennzeichnet, daß das Energiebündel ein Elektronenbündel (7) ist.
3. Verfahren nach Anspruch 2, dadurch gekennzeichnet, daß die Bildelektrode (17) vom Elektronenbündel (7) aufgeladen wird, und daß die gute oder nicht gute Wirkung des Schaltelements (13, 22, 23, 24) durch Entladen der Bildelektrode (17) über das Schaltelement (13, 22, 23, 24) geprüft wird.
4. Verfahren nach Anspruch 2, dadurch gekennzeichnet, daß die Bildelektrode (17) über das Schaltelement (13, 22, 23, 24) mit einer Ladung versehen wird, und daß die Lieferung der



again by means of a laser beam.

The invention is of course not limited to the examples shown but several variations which are all known to those skilled in the art are possible within the scope of the invention. Switching elements such as diode rings can be alternatively tested by means of laser radiation; a condition is that the diodes associated with the diode ring are laterally separated. The method described with reference to Fig. 2 may be alternatively used for switching elements other than diodes such as, for example, varistors, MIMs or other dipoles. Likewise the field effect transistors in the example of Fig. 1 may be replaced by other threepoles. In a possibility auxiliary circuit 8 the number of photodiodes 19 may be alternatively reduced by connecting one photodiodes 11, whilst radiation-sensitive resistors instead of photodiodes can be used alternatively. Finally the parts of the devices to be tested need not necessarily form part of a display device which is organised as a matrix, whilst the invention can be alternatively used for display devices other than liquid crystalline devices.

Claims

1. A method of testing by means of an energy beam (5, 7) a part of a display device (10) comprising a picture electrode (17) of a pixel to be formed and a switching element (13, 22, 23, 24) between at least one drive line (11, 12) and the picture electrode (17) characterized in that the switching element (13, 22, 23, 24) is tested by scanning the switching element (13, 22, 23, 24) or the picture electrode (17) by means of said energy beam (5, 7) in order to detect the functioning or non-functioning of the switching element (13, 22, 23, 24).
2. A method as claimed in Claim 1, characterized in that the energy beam is an electron beam (7).
3. A method as claimed in Claim 2, characterized in that the picture electrode (17) is charged by the electron beam (7) and in that the functioning or non-functioning of the switching element (13, 22, 23, 24) is tested by discharging the picture electrode (17) via the switching element (13, 22, 23, 24).
4. A method as claimed in Claim 2, characterized in that the picture electrode (17) is provided with a charge via the switching element (13, 22, 23, 24) and in that the supply of charge to the picture electrode (17) is tested by means of a scanning electron microscope.
5. A method as claimed in Claim 1, characterized in that the energy beam is a light beam (5), particularly a laser beam.
6. A method as claimed in Claim 5, characterized in that the switching element (13, 22, 23, 24) includes at least one photosensitive semiconductor element which is scanned by the light beam (5).
7. A method as claimed in Claims 1 to 6, characterized in that the switching element (13, 22, 23, 24) comprises redundant elements which, dependent on the test result, can be incorporated in or removed from the interconnection between the drive line (11, 12) and the picture electrode (17).
8. A method as claimed in Claim 7, characterized in that a laser beam is used for establishing or interrupting the interconnection.
9. A method as claimed in Claims 5 to 8, characterized in that the photosensitive semiconductor elements are laterally separated.

Patentansprüche

1. Verfahren zum Prüfen mittels eines Energiebündels (5, 7) eines Teils einer Anzeigeanordnung (10), mit einer Bildelektrode (17) eines zu formenden Bildelements und mit einem Schaltelement (13, 22, 23, 24) zwischen wenigstens einer Steuerleitung (11, 12) und der Bildelektrode (17), dadurch gekennzeichnet, daß das Schaltelement (13, 22, 23, 24) durch Abtasten des Schaltelements (13, 22, 23, 24) oder der Bildelektrode (17) mittels des Energiebündels (5, 7) geprüft wird, um die gute oder nicht gute Wirkung des Schaltelements (13, 22, 23, 24) zu detektieren.
2. Verfahren nach Anspruch 1, dadurch gekennzeichnet, daß das Energiebündel ein Elektronenbündel (7) ist.
3. Verfahren nach Anspruch 2, dadurch gekennzeichnet, daß die Bildelektrode (17) vom Elektronenbündel (7) aufgeladen wird, und daß die gute oder nicht gute Wirkung des Schaltelements (13, 22, 23, 24) durch Entladen der Bildelektrode (17) über das Schaltelement (13, 22, 23, 24) geprüft wird.
4. Verfahren nach Anspruch 2, dadurch gekennzeichnet, daß die Bildelektrode (17) über das Schaltelement (13, 22, 23, 24) mit einer Ladung versehen wird, und daß die Lieferung der

Ladung zur Bildelektrode (17) mit Hilfe eines Rasterelektronenmikroskops geprüft wird.

5. Verfahren nach Anspruch 1, dadurch gekennzeichnet, daß das Energiebündel ein Lichtbündel (5) ist, und insbesondere ein Laserbündel.
6. Verfahren nach Anspruch 5, dadurch gekennzeichnet, daß das Schaltelement (13, 22, 23, 24) wenigstens ein photoempfindliches Halbleiterelement enthält, das vom Lichtbündel (5) abgetastet wird.
7. Verfahren nach Anspruch 1 bis 6, dadurch gekennzeichnet, daß das Schaltelement (13, 22, 23, 24) redundante Elemente enthält, die abhängig vom Prüfergebnis in die Verbindung zwischen der Steuerleitung (11, 12) und der Bildelektrode (17) eingeschaltet oder daraus entfernt werden können.
8. Verfahren nach Anspruch 7, dadurch gekennzeichnet, daß ein Laserbündel zum Herstellen oder Unterbrechen der Verbindung verwendet wird.
9. Verfahren nach Anspruch 5 bis 8, dadurch gekennzeichnet, daß die photoempfindlichen Halbleiterelemente lateral voneinander getrennt werden.

Revendications

1. Procédé pour tester au moyen d'un faisceau d'énergie (5, 7) une partie d'un dispositif d'affichage (10) comprenant une électrode d'image (17) d'un pixel à former et un élément de commutation (13, 22, 23, 24) entre au moins une ligne d'activation (11, 12) et l'électrode d'image (17), caractérisé en ce qu'on teste l'élément de commutation (13, 22, 23, 24) en balayant l'élément de commutation (13, 22, 23, 24) ou l'électrode d'image (17) au moyen du faisceau d'énergie (5, 7) afin de détecter le fonctionnement ou le non-fonctionnement de l'élément de commutation (13, 22, 23, 24).
2. Procédé suivant la revendication 1, caractérisé en ce que le faisceau d'énergie est un faisceau d'électrons (7).
3. Procédé suivant la revendication 2, caractérisé en ce que l'électrode d'image (17) est chargée par le faisceau d'électrons (7) et en ce que le fonctionnement ou le non-fonctionnement de l'élément de commutation (13, 22, 23, 24) est testé en déchargeant l'électrode d'image (17) par l'intermédiaire de l'élément de commuta-

tion (13, 22, 23, 24).

4. Procédé suivant la revendication 2, caractérisé en ce que l'électrode d'image (17) est pourvue d'une charge par l'intermédiaire de l'élément de commutation (13, 22, 23, 24) et en ce que la fourniture de la charge à l'électrode d'image (17) est testée au moyen d'un microscope électronique à balayage.
5. Procédé suivant la revendication 1, caractérisé en ce que le faisceau d'énergie est un faisceau lumineux (5), en particulier un faisceau laser.
6. Procédé suivant la revendication 5, caractérisé en ce que l'élément de commutation (13, 22, 23, 24) comprend au moins un élément semi-conducteur photosensible qui est balayé par le faisceau lumineux (5).
7. Procédé suivant les revendications 1 à 6, caractérisé en ce que l'élément de commutation (13, 22, 23, 24) comprend des éléments redondants qui, en fonction du résultat de test, peuvent être incorporés dans l'interconnexion entre la ligne d'activation (11, 12) et l'électrode d'image (17) ou être retirés de cette interconnexion.
8. Procédé suivant la revendication 7, caractérisé en ce qu'un faisceau laser est utilisé pour établir ou interrompre l'interconnexion.
9. Procédé suivant les revendications 5 à 8, caractérisé en ce que les éléments semi-conducteurs photosensibles sont séparés latéralement.

